P-Channel Power MOSFET

FEATURES

- Advance trench process technology
- RoHS compliant
- Halogen-free

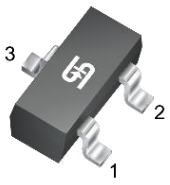
APPLICATIONS

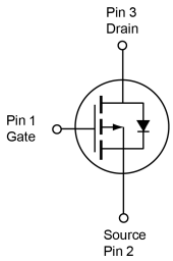
- Power management
- Load switch
- Battery protection

KEY PERFORMANCE PARAMETERS			
PARAMETER		**VALUE**	**UNIT**
V_{DS}		-20	V
$R_{DS(on)}$ (max)	V_{GS} = -4.5V	39	mΩ
	V_{GS} = -2.5V	52	
	V_{GS} = -1.8V	68	
Q_g		9.5	nC

Pb-Free RoHS COMPLIANT HALOGEN FREE

SOT-23





Note: MSL 1 (Moisture Sensitivity Level) per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)				
PARAMETER		**SYMBOL**	**LIMIT**	**UNIT**
Drain-Source Voltage		V_{DS}	-20	V
Gate-Source Voltage		V_{GS}	±8	V
Continuous Drain Current	T_A = 25°C	I_D	-4.3	A
Pulsed Drain Current (Note 1)		I_{DM}	-17.2	A
Total Power Dissipation	T_A = 25°C	P_D	1.04	W
	T_A = 70°C		0.67	
Operating Junction and Storage Temperature Range		T_J, T_{STG}	- 55 to +150	°C

THERMAL PERFORMANCE			
PARAMETER	**SYMBOL**	**LIMIT**	**UNIT**
Junction to Ambient Thermal Resistance (Note 2)	$R_{\Theta JA}$	120	°C/W

Notes:

1. Pulse Width ≤ 100μs.
2. Device on a PCB FR4 with 1 in^2 (single layer, 2 oz thickness) copper area for drain connection.

ELECTRICAL SPECIFICATIONS (T_A = 25°C unless otherwise noted)						
PARAMETER	**CONDITIONS**	**SYMBOL**	**MIN**	**TYP**	**MAX**	**UNIT**
Static (Note 3)						
Drain-Source Breakdown Voltage	V_{GS} = 0V, I_D = -250μA	BV_{DSS}	-20	--	--	V
Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = -250μA	$V_{GS(TH)}$	-0.4	-0.6	-1	V
Gate Body Leakage	V_{GS} = ±8V, V_{DS} = 0V	I_{GSS}	--	--	±100	nA
Zero Gate Voltage Drain Current	V_{DS} = -20V, V_{GS} = 0V	I_{DSS}	--	--	-1	μA
Drain-Source On-State Resistance	V_{GS} = -4.5V, I_D = -4.3A	$R_{DS(on)}$	--	28	39	mΩ
	V_{GS} = -2.5V, I_D = -3.7A		--	36	52	
	V_{GS} = -1.8V, I_D = -2.9A		--	46	68	
Forward Transconductance	V_{DS} = -10V, I_D = -1.1A	g_{fs}	--	9.2	--	S
Dynamic (Note 4)						
Total Gate Charge	V_{DS} = -10V, I_D = -4.3A, V_{GS} = -4.5V	Q_g	--	9.5	--	nC
Gate-Source Charge		Q_{gs}	--	0.9	--	
Gate-Drain Charge		Q_{gd}	--	2.6	--	
Input Capacitance	V_{DS} = -10V, V_{GS} = 0V, f = 1.0MHz	C_{iss}	--	769	--	pF
Output Capacitance		C_{oss}	--	112	--	
Reverse Transfer Capacitance		C_{rss}	--	106	--	
Switching (Note 5)						
Turn-On Delay Time	V_{DD} = -10V, R_G = 6Ω, I_D = -4.3A, V_{GS} = -4.5V	$t_{d(on)}$	--	4.6	--	ns
Turn-On Rise Time		t_r	--	36	--	
Turn-Off Delay Time		$t_{d(off)}$	--	83	--	
Turn-Off Fall Time		t_f	--	56	--	
Source-Drain Diode						
Forward Voltage (Note 3)	I_S = -4.3A, V_{GS} = 0V	V_{SD}	--	0.7	1.2	V

Notes:

3. Pulse test: Pulse Width ≤ 300μs, duty cycle ≤ 2%.
4. Defined by design. Not subject to production test.
5. Switching time is essentially independent of operating temperature.

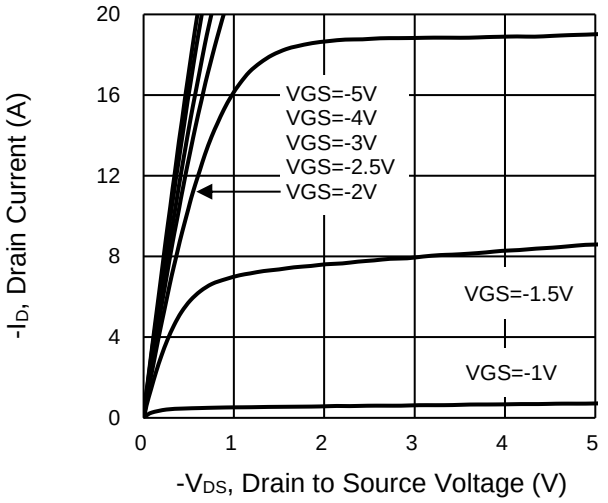
ORDERING INFORMATION

ORDERING CODE	PACKAGE	PACKING
TSM2323CX RFG	SOT-23	3kpcs / 7” Reel

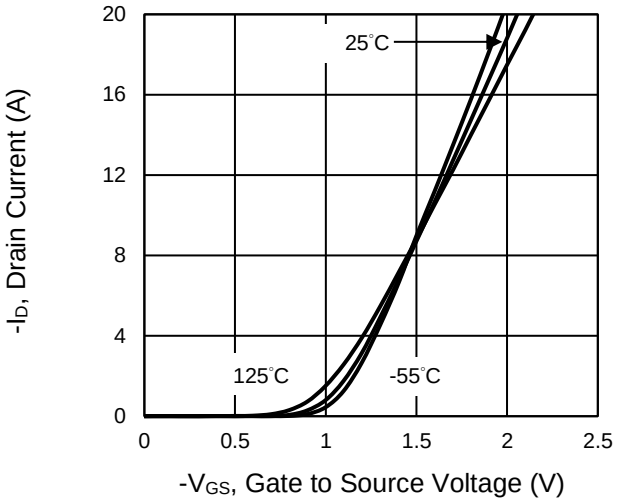
CHARACTERISTICS CURVES

(T_A = 25°C unless otherwise noted)

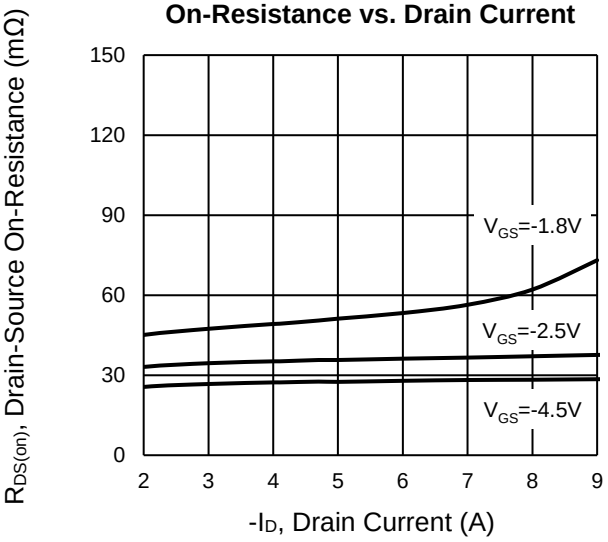
Output Characteristics



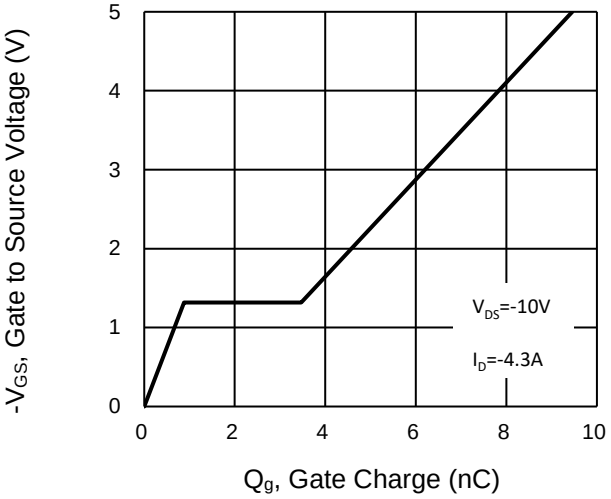
Transfer Characteristics



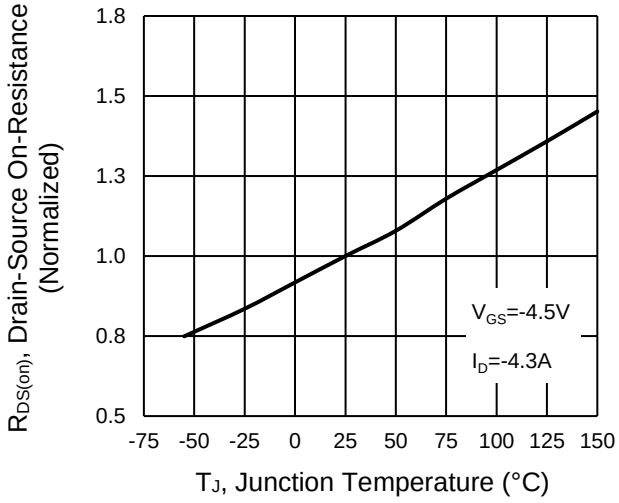
On-Resistance vs. Drain Current



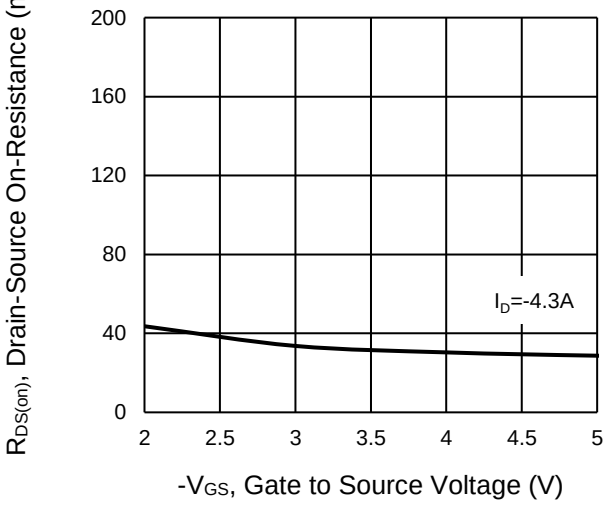
Gate-Source Voltage vs. Gate Charge



On-Resistance vs. Junction Temperature



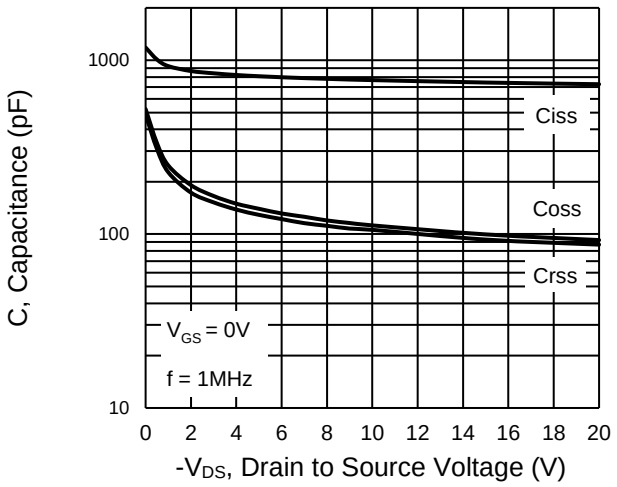
On-Resistance vs. Gate-Source Voltage



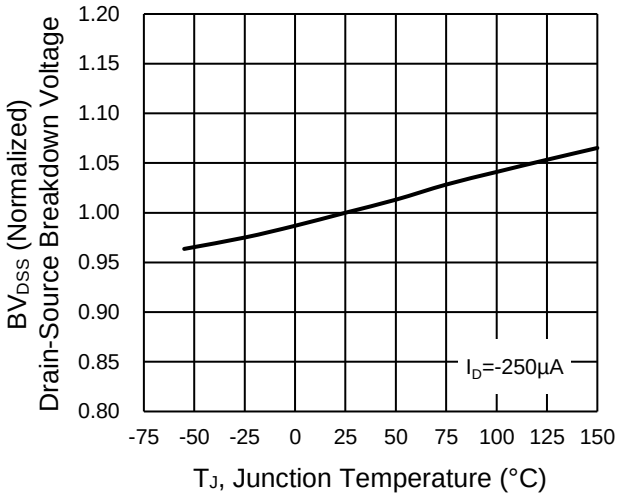
CHARACTERISTICS CURVES

(T_A = 25°C unless otherwise noted)

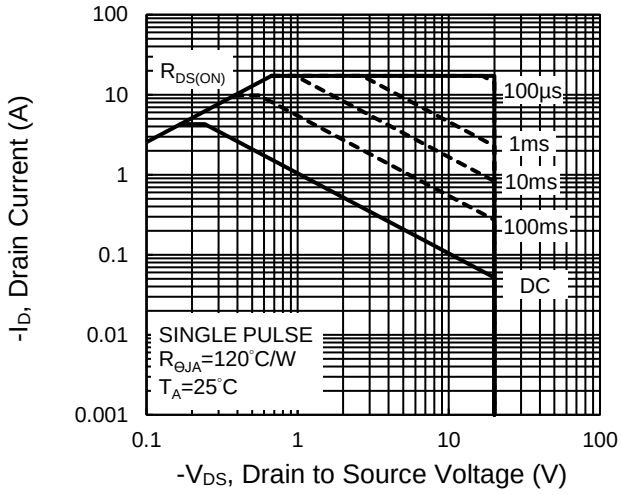
Capacitance vs. Drain-Source Voltage



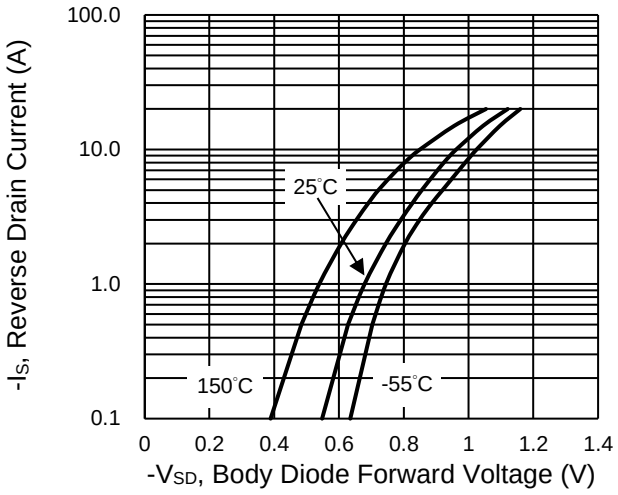
BV_{DSS} vs. Junction Temperature



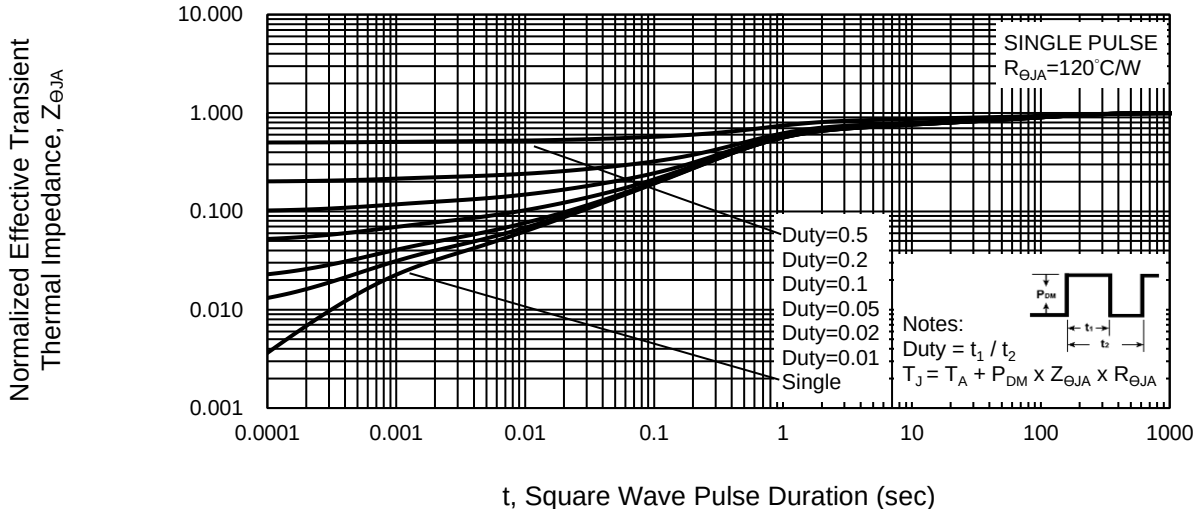
Maximum Safe Operating Area, Junction-to-Ambient



Source-Drain Diode Forward Current vs. Voltage



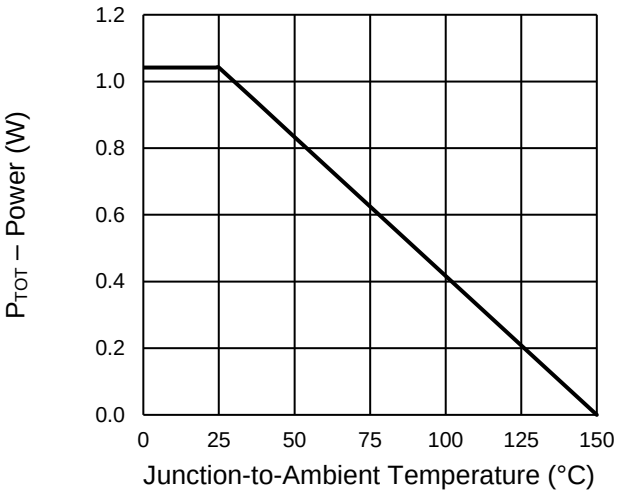
Normalized Thermal Transient Impedance, Junction-to-Ambient



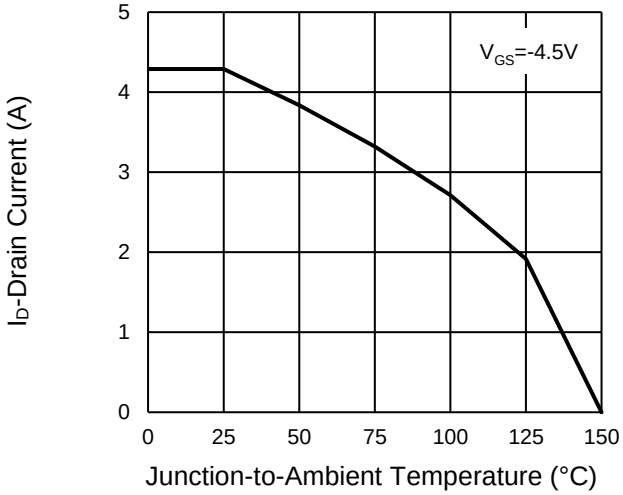
CHARACTERISTICS CURVES

(T_A = 25°C unless otherwise noted)

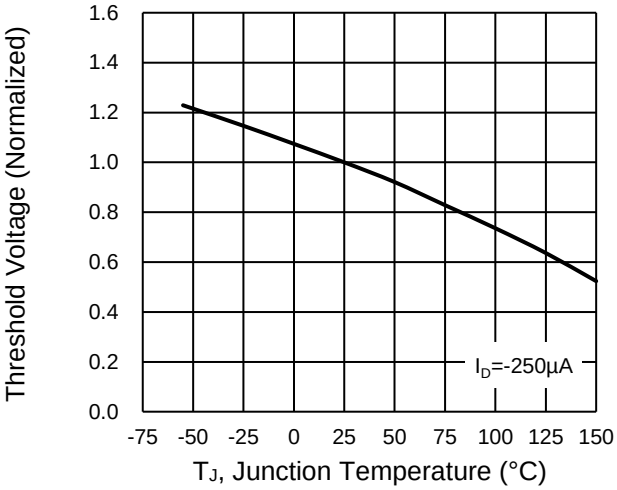
Power Dissipation



Drain Current

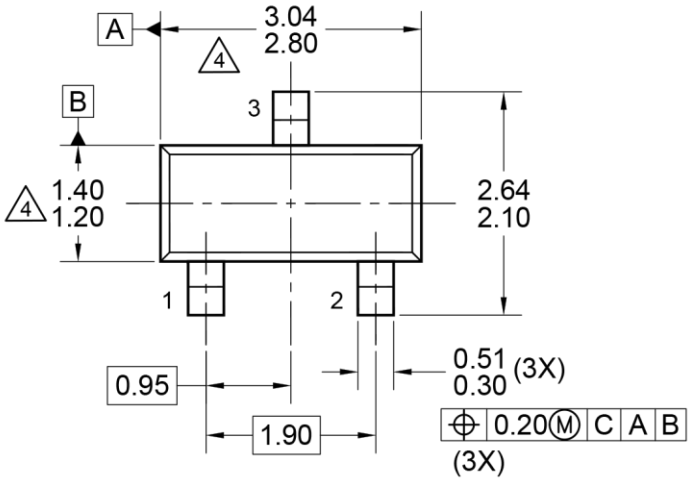


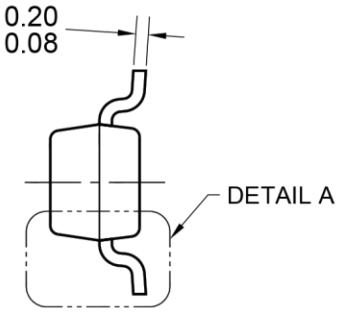
Normalized gate threshold voltage vs Temperature

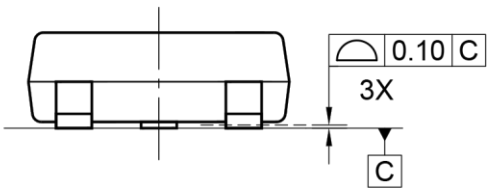


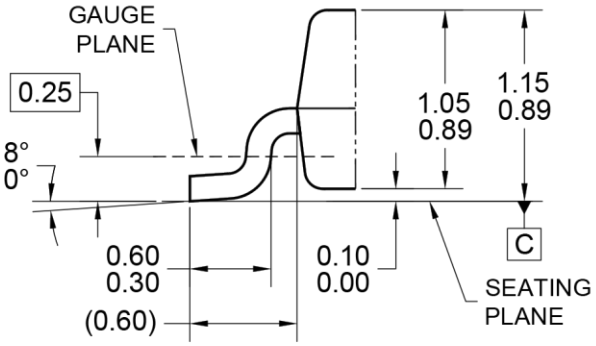
PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

SOT-23

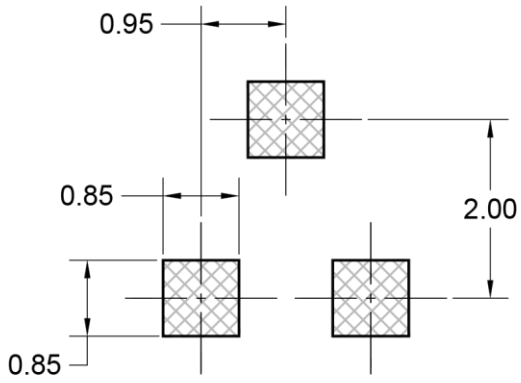




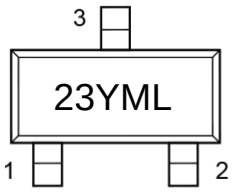




DETAIL A, ROTATED -90°
(SCALE 2:1)



SUGGESTED PAD LAYOUT



MARKING DIAGRAM

NOTES: UNLESS OTHERWISE SPECIFIED

1. ALL DIMENSIONS ARE IN MILLIMETERS.
2. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
3. PACKAGE OUTLINE REFERENCE: JEDEC TO-236, ISSUE H, VARIATION AA.
4. MOLDED PLASTIC BODY DIMENSIONS DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
5. DWG NO. REF: HQ2SD07-SOT23JEDEC-104 REV A.

23 = Device marking
Y = Year Code
M = Month Code for Halogen Free Product
(O=Jan, P=Feb, Q=Mar, R=Apl, S=May, T=Jun, U=Jul, V=Aug, W=Sep, X=Oct, Y=Nov, Z=Dec)
L = Lot Code

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